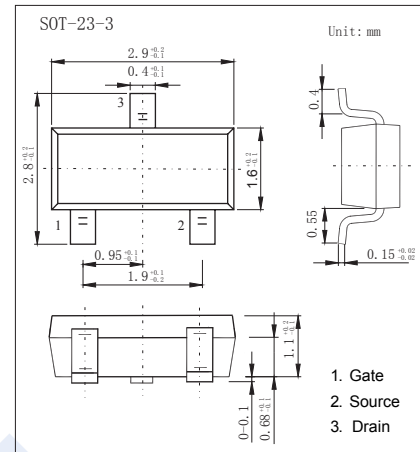
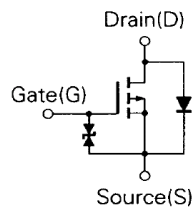


P-Channel MOSFET

2SJ461

■ Features

- $V_{DS} (V) \approx -50V$
- $I_D \approx -0.1 A$
- $R_{DS(ON)} < 50 \Omega$ ($V_{GS} = -4V$)
- $R_{DS(ON)} < 100 \Omega$ ($V_{GS} = -2.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-50	V
Gate-Source Voltage	V_{GS}	± 7	
Continuous Drain Current	I_D	-0.1	A
Pulsed Drain Current (Note.1)	I_{DM}	-0.2	
Power Dissipation	P_D	0.2	W
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10$ ms, duty cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -250 \mu A, V_{GS} = 0V$	-50			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -50V, V_{GS} = 0V$			-1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 7V$			± 3	μA
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{GS} = -3V, I_D = -1mA$	-0.7		-1.3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4V, I_D = -10mA$			50	Ω
		$V_{GS} = -2.5V, I_D = -3mA$			100	
Forward Transconductance	g_{FS}	$V_{DS} = -3V, I_D = -10mA$	12			mS
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -3V, f = 1MHz$		6		pF
Output Capacitance	C_{oss}			9		
Reverse Transfer Capacitance	C_{rss}			1.6		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS(on)} = -3V, I_D = -20mA, R_L = 200 \Omega, R_G = 10 \Omega, V_{DD} = -3V$		32		ns
Turn-On Rise Time	t_r			270		
Turn-Off DelayTime	$t_{d(off)}$			45		
Turn-Off Fall Time	t_f			130		

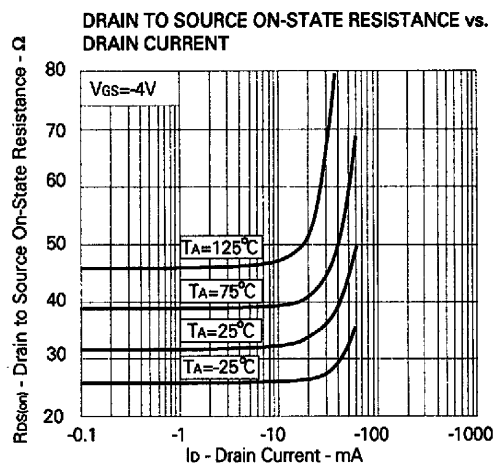
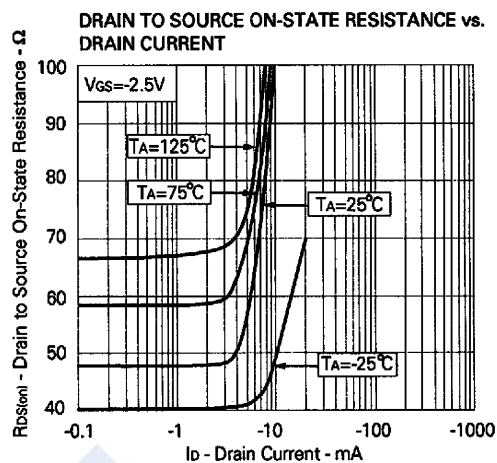
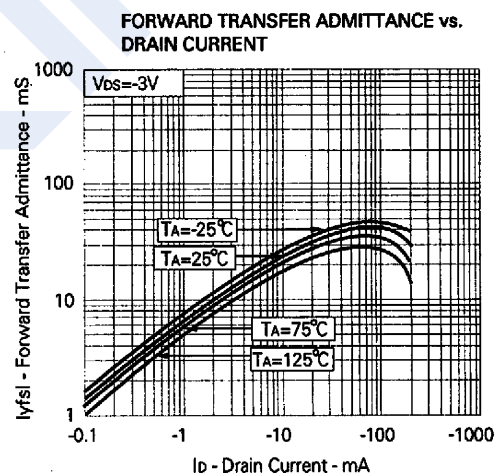
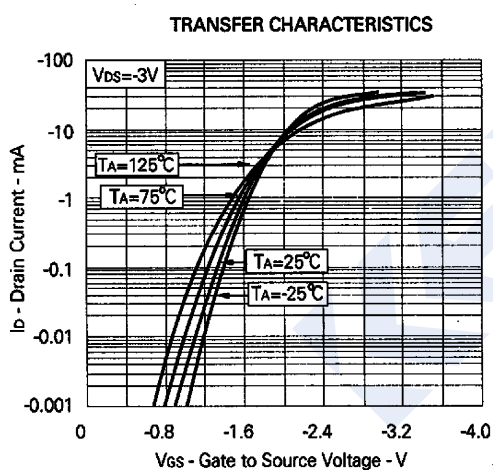
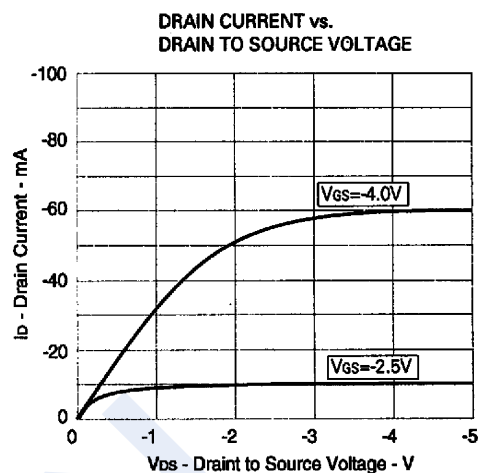
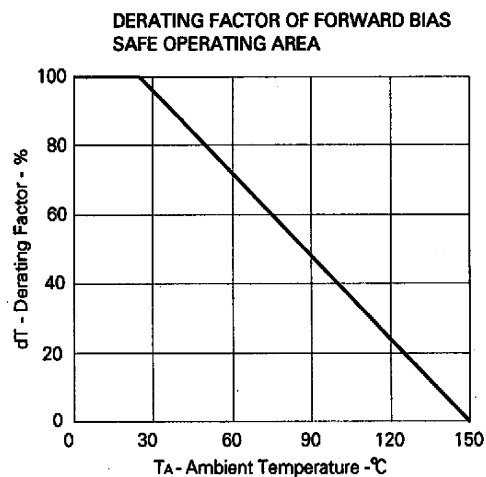
■ Marking

Marking	H19
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P-Channel MOSFET

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■ Typical Characteristics



P-Channel MOSFET

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■ Typical Characteristics

